

### Important notice

Dear Customer,

On 7 February 2017 the former NXP Standard Product business became a new company with the tradename **Nexperia**. Nexperia is an industry leading supplier of Discrete, Logic and PowerMOS semiconductors with its focus on the automotive, industrial, computing, consumer and wearable application markets

In data sheets and application notes which still contain NXP or Philips Semiconductors references, use the references to Nexperia, as shown below.

Instead of <a href="http://www.nxp.com">http://www.nxp.com</a>, <a href="http://www.semiconductors.philips.com/">http://www.nxp.com</a>, <a href="http://www.nexperia.com/">http://www.nexperia.com/</a>, <a href="http://www.nexperia.com/">http://www.nexperia.com/</a>, <a href="http://www.nexperia.com/">use http://www.nexperia.com/</a>

Instead of sales.addresses@www.nxp.com or sales.addresses@www.semiconductors.philips.com, use salesaddresses@nexperia.com (email)

Replace the copyright notice at the bottom of each page or elsewhere in the document, depending on the version, as shown below:

- © NXP N.V. (year). All rights reserved or © Koninklijke Philips Electronics N.V. (year). All rights reserved

Should be replaced with:

- © Nexperia B.V. (year). All rights reserved.

If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

# **DISCRETE SEMICONDUCTORS**

# DATA SHEET

**PEMD4; PUMD4** NPN/PNP resistor-equipped transistors; R1 = 10 kΩ, R2 = open

Product data sheet Supersedes data of 2002 Jan 14 2003 Oct 10



# NPN/PNP resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = open

PEMD4; PUMD4

#### **FEATURES**

- Built-in bias resistors
- Simplified circuit design
- · Reduction of component count
- · Reduced pick and place costs.

# **APPLICATIONS**

- · Low current peripheral driver
- Replacement for general purpose transistors in digital applications
- . Control of IC inputs.

#### QUICK REFERENCE DATA

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
$V_{CEO}$	collector-emitter voltage	_	50	V
I <sub>O</sub>	output current (DC)	ı	100	mA
TR1	NPN	_	_	_
TR2	PNP	ı	ı	ı
R1	bias resistor	10		kΩ
R2	open	_	_	_

#### **DESCRIPTION**

NPN/PNP resistor-equipped transistors (see "Simplified outline, symbol and pinning" for package details).

#### PRODUCT OVERVIEW

TYPE	PACKAGE		MARKING CODE	PNP/PNP	NPN/NPN
NUMBER	PHILIPS	EIAJ	WARKING CODE	COMPLEMENT	COMPLEMENT
PEMD4	SOT666		23	PEMB4	PEMH4
PUMD4	SOT363	SC-88	D*4	PUMB4	PUMH4

# Note

- \* = p: Made in Hong Kong.
  - \* = t: Made in Malaysia.
  - \* = W: Made in China.

# SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL	PINNING		
TIPE NOWIBER	SIMIFLIFIED OUTLINE AND STMBOL	PIN	DESCRIPTION	
PEMD4 PUMD4	6 5 4 6 5 4	1 2	emitter TR1 base TR1	
i omb i	R1	3	collector TR2	
	TR1	4 5	emitter TR2 base TR2	
		6	collector TR1	
	Top view MDB814			

# NPN/PNP resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = open

PEMD4; PUMD4

# **ORDERING INFORMATION**

TYPE NUMBER		PACKAGE	
NAME		DESCRIPTION	VERSION
PEMD4	_	plastic surface mounted package; 6 leads	SOT666
PUMD4	_	plastic surface mounted package; 6 leads	SOT363

#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT			
Per transist	Per transistor; for the PNP transistor with negative polarity							
V <sub>CBO</sub>	collector-base voltage	open emitter	_	50	V			
V <sub>CEO</sub>	collector-emitter voltage	open base	_	50	V			
V <sub>EBO</sub>	emitter-base voltage	open collector	_	5	V			
Io	output current (DC)		_	100	mA			
I <sub>CM</sub>	peak collector current		_	100	mA			
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C						
	SOT363	note 1	_	200	mW			
	SOT666	notes 1 and 2	_	200	mW			
T <sub>stg</sub>	storage temperature		-65	+150	°C			
T <sub>j</sub>	junction temperature		_	150	°C			
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C			
Per device								
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C						
	SOT363	note 1	_	300	mW			
	SOT666	notes 1 and 2	_	300	mW			

# **Notes**

- 1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.
- 2. Reflow soldering is the only recommended soldering method.

# NPN/PNP resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = open

PEMD4; PUMD4

# THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
Per transis	stor			
R <sub>th j-a</sub>	thermal resistance from junction to ambient	T <sub>amb</sub> ≤ 25 °C		
	SOT363	note 1	625	K/W
	SOT666	notes 1 and 2	625	K/W
Per device				
R <sub>th j-a</sub>	thermal resistance from junction to ambient	T <sub>amb</sub> ≤ 25 °C		
	SOT363	note 1	416	K/W
	SOT666	notes 1 and 2	416	K/W

#### **Notes**

- 1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.
- 2. Reflow soldering is the only recommended soldering method.

### **CHARACTERISTICS**

 $T_{amb}$  = 25 °C unless otherwise specified.

SYMBOL	PARAMETER CONDITIONS		MIN.	TYP.	MAX.	UNIT		
Per transis	Per transistor; for the PNP transistor with negative polarity							
I <sub>CBO</sub>	collector-base cut-off current	V <sub>CB</sub> = 50 V; I <sub>E</sub> = 0	_	_	100	nA		
I <sub>CEO</sub>	collector-emitter cut-off current	V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0	-	-	1	μΑ		
		$V_{CE} = 30 \text{ V}; I_{B} = 0; T_{j} = 150 ^{\circ}\text{C}$	_	_	50	μΑ		
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0$	_	_	100	nA		
h <sub>FE</sub>	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 1 \text{ mA}$	200	_	-			
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	_	_	150	mV		
R1	input resistor		7	10	13	kΩ		
C <sub>c</sub>	collector capacitance	$I_E = i_e = 0$ ; $V_{CB} = 10 \text{ V}$ ; $f = 1 \text{ MHz}$						
	TR1 (NPN)		_	_	2.5	pF		
	TR2 (PNP)		_	_	3	pF		

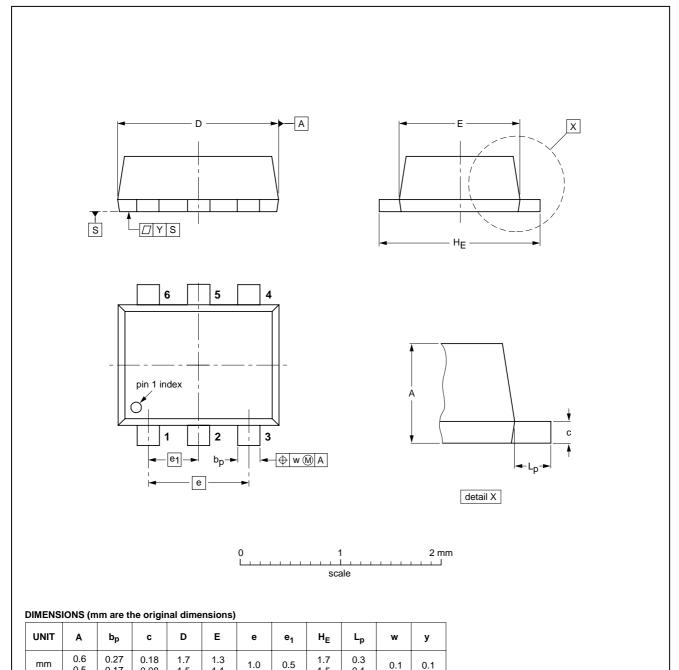
# NPN/PNP resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = open

PEMD4; PUMD4

# **PACKAGE OUTLINES**

Plastic surface mounted package; 6 leads

SOT666



OUTLINE		REFERENCES			EUROPEAN ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE	
SOT666						<del>01-01-04</del> 01-08-27	

1.5

2003 Oct 10 5

0.17

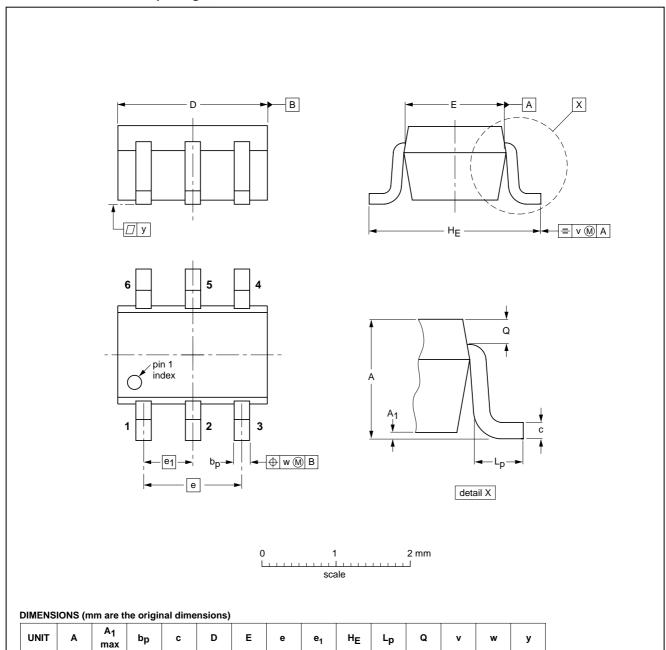
0.08

# NPN/PNP resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = open

PEMD4; PUMD4

# Plastic surface mounted package; 6 leads

**SOT363** 



OUTLINE		REFER	FERENCES EUROPEAN			ISSUE DATE
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT363			SC-88			97-02-28

0.65

1.3

0.45

0.15

0.2

0.2

0.1

2003 Oct 10 6

0.30

0.20

0.1

8.0

mm

0.25

# NPN/PNP resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = open

PEMD4; PUMD4

#### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

#### **Notes**

- 1. Please consult the most recently issued document before initiating or completing a design.
- 2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

### **DISCLAIMERS**

**General** — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

**Applications** — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) may cause permanent damage to the device. Limiting values are stress ratings only and operation of the device at these or any other conditions

above those given in the Characteristics sections of this document is not implied. Exposure to limiting values for extended periods may affect device reliability.

Terms and conditions of sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nxp.com/profile/terms, including those pertaining to warranty, intellectual property rights infringement and limitation of liability, unless explicitly otherwise agreed to in writing by NXP Semiconductors. In case of any inconsistency or conflict between information in this document and such terms and conditions, the latter will prevail.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

**Export control** — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from national authorities.

**Quick reference data** — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

# **NXP Semiconductors**

# **Customer notification**

This data sheet was changed to reflect the new company name NXP Semiconductors. No changes were made to the content, except for the legal definitions and disclaimers.

# **Contact information**

For additional information please visit: http://www.nxp.com

For sales offices addresses send e-mail to: salesaddresses@nxp.com

© NXP B.V. 2009

All rights are reserved. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner.

The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice. No liability will be accepted by the publisher for any consequence of its use. Publication thereof does not convey nor imply any license under patent- or other industrial or intellectual property rights.

Printed in The Netherlands R75/02/pp8 Date of release: 2003 Oct 10 Document order number: 9397 750 11826



# **Mouser Electronics**

**Authorized Distributor** 

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Nexperia: PEMD4-QX